

DHG40B1200LB

preliminary

 $V_{RRM} = 1200 V$

 $I_{DAV} = 34 A$

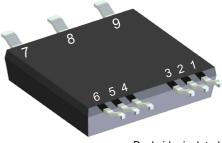
 t_{rr} = 150 ns

High Performance Fast Recovery Diode Low Loss and Soft Recovery 1~ Rectifier Bridge

Sonic Fast Recovery Diode

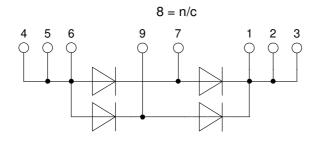
Part number

DHG40B1200LB



Backside: isolated





Features / Advantages:

- Planar passivated chips
- Very low leakage current
- Very short recovery time
- Improved thermal behaviour
- Very low Irm-values
- Very soft recovery behaviour
- Avalanche voltage rated for reliable operation
- Soft reverse recovery for low EMI/RFI
- Low Irm reduces:
 - Power dissipation within the diode
- Turn-on loss in the commutating switch

Applications:

- Antiparallel diode for high frequency switching devices
- Antisaturation diode
- Snubber diode
- Free wheeling diode
- Rectifiers in switch mode power supplies (SMPS)
- Uninterruptible power supplies (UPS)

Package: SMPD

- Isolation Voltage: 3000 V~
- Industry convenient outline
- RoHS compliant
- Epoxy meets UL 94V-0
- Soldering pins for PCB mounting
- Backside: DCB ceramic
- Reduced weight
- Advanced power cycling

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IXYS A Littelfuse Technology

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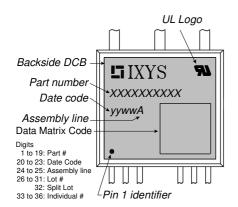
Fast Diode					Ratings			
Symbol	Definition	Conditions		min.	typ.	max.	Unit	
V _{RSM}	max. non-repetitive reverse blocki	ing voltage	$T_{VJ} = 25^{\circ}C$			1200	V	
V_{RRM}	max. repetitive reverse blocking v	oltage	$T_{VJ} = 25^{\circ}C$			1200	V	
I _R	reverse current, drain current	V _R = 1200 V	$T_{VJ} = 25^{\circ}C$			40	μΑ	
		$V_R = 1200 \text{ V}$	$T_{VJ} = 125^{\circ}C$			0.4	mΑ	
V _F	forward voltage drop	I _F = 20 A	$T_{VJ} = 25^{\circ}C$			2.24	V	
		$I_F = 40 \text{ A}$				2.89	٧	
		I _F = 20 A	T _{vJ} = 125°C			2.24	٧	
		$I_F = 40 \text{ A}$				3.15	٧	
IDAV	bridge output current	$T_{c} = 80^{\circ}C$	T _{vJ} = 150°C			34	Α	
		rectangular $d = 0.5$					i 	
V _{F0}	threshold voltage slope resistance for power loss calculation only		T _{VJ} = 150°C			1.35	٧	
r _F						43	mΩ	
R _{thJC}	thermal resistance junction to case					1.5	K/W	
R _{thCH}	thermal resistance case to heatsir			0.50		K/W		
P _{tot}	total power dissipation		$T_C = 25^{\circ}C$			80	W	
I _{FSM}	max. forward surge current	$t = 10 \text{ ms}$; (50 Hz), sine; $V_R = 0 \text{ V}$	$T_{VJ} = 45^{\circ}C$			150	Α	
CJ	junction capacitance	$V_R = 600 \text{V} f = 1 \text{MHz}$	$T_{VJ} = 25^{\circ}C$		8		pF	
I _{RM}	max. reverse recovery current	\	$T_{VJ} = 25 ^{\circ}\text{C}$		15		Α	
	($I_F = 15 \text{ A}; V_R = 600 \text{ V}$	$T_{VJ} = 125$ °C		20		Α	
t _{rr}	reverse recovery time	$\begin{cases} I_F = 15 \text{ A}; V_R = 600 \text{ V} \\ -di_F /dt = 600 \text{ A}/\mu\text{s} \end{cases}$	$T_{VJ} = 25 ^{\circ}C$		150		ns	
)	$T_{VJ} = 125$ °C		250		ns	



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Package SMPD				ı	Ratings			
Symbol	Definition	Conditions		min.	typ.	max.	Unit	
I _{RMS}	RMS current	per terminal				100	Α	
T _{VJ}	virtual junction temperature			-55		150	°C	
T _{op}	operation temperature			-55		125	°C	
T _{stg}	storage temperature			-55		150	°C	
Weight					8.5		g	
F _c	mounting force with clip			40		130	N	
d _{Spp/App}	creepage distance on surface striking distance through air		terminal to terminal	1.6			mm	
$d_{\text{Spb/Apb}}$			terminal to backside	4.0			mm	
V _{ISOL}	isolation voltage	t = 1 second	50/60 Hz. RMS: IIsoi ≤ 1 mA	3000			٧	
		t = 1 minute		2500			٧	



Part description

D = Diode

H = Sonic Fast Recovery Diode

G = extreme fast

40 = Current Rating [A]

B = 1~ Rectifier Bridge 1200 = Reverse Voltage [V]

LB = SMPD-B

Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	DHG40B1200LB-TUB	DHG40B1200LB-TUB	Tube	20	525198
Alternative	DHG40B1200LB-TRR	DHG40B1200LB	Tape & Reel	200	524922

Equivalent Circuits for Simulation			* on die level	$T_{VJ} = 150 ^{\circ}\text{C}$
$I \rightarrow V_0$)—[R ₀]–	Fast Diode		
V _{0 max}	threshold voltage	1.35		V
$R_{0 \text{ max}}$	slope resistance *	41		$m\Omega$